APS Satellite Meeting, 2022, ICTS Bangalore

Broken-symmetry states at half-integer band fillings in twisted bilayer graphene

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Funding



Reference

Bhowmik et al. arXiv:2108.12689, 2021 [Nature Physics, In Press]

New phenomenology at fractional fillings in zero magnetic field

Fractional Quantum Hall States at Zero Magnetic Field

Titus Neupert,¹ Luiz Santos,² Claudio Chamon,³ and Christopher Mudry¹ ¹Condensed Matter Theory Group, Paul Scherrer Institute, CH-5232 Villigen PSI, Switzerland ²Department of Physics, Harvard University, 17 Oxford Street, Cambridge, Massachusetts 02138, USA ³Physics Department, Boston University, Boston, Massachusetts 02215, USA (Received 22 December 2010; published 6 June 2011)

Nearly Flatbands with Nontrivial Topology

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Low-energy ultra flat bands are essential ingredient

Carr et al. PhysRevB.98.085144 (2018)

Novel phases within moiré flat bands at zero B-field



Phases are tunable with dielectric environment



Basic electrical characterization of the devices



• Peaks in resistance at integer fillings.

• Twist angle homogeneity across various contact configurations.

States at half-integer band fillings at low B-field



States at half-integer band fillings at low B-field



- Sign-reversal at v = 0.5 and 3.5.
- They persist down to B = 0.3 T.

Sign-reversal at v = +/-3.5 at low field in device D2



v = +/-3.5 persists throughout the entire B-field range



Landau Fan diagram



- Linearly dispersing resistance minima from integer fillings.
- A new state appears at v = -0.5

Correlated Chern Insulators



Zero-field thermoelectricity



 The state at v = 3.5 appears at B = 0 T.

Ghawri, B. et al. (*Nature Communications,* In Press, arXiv:2004.12356)



Spin/charge density-driven doubled unit cell



Theory calculations by Jeil Jung, Nicolas Leconte, S. Appalakondaiah, Dongkyu Lee (University of Seoul)

Summary

- Translational symmetry-broken states appear at half-integer fillings.
- They persist down to zero field which suggests the existence of a spin/charge density wave ground state.
- TMDC dielectrics may be a promising pathway to realize correlated states at fractional fillings.

"Emergence of broken-symmetry states at half-integer band fillings in twisted bilayer graphene" (arXiv:2108.12689, 2021) [Nature Physics, In Press]

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hBN crystal: Takashi Taniguchi (Research Center for Functional Materials, NIMS, Japan) Kenji Watanabe (International Center for Materials Nanoarchitectonics, NIMS, Japan)